$\begin{array}{|c|c|c|c|c|c|c|c|c|} \hline & \text{PHIL_BJT} \ r_o = 10,91814 \text{k}\Omega \ V_A = 51,82703 \text{V} \ I_{C_{sat}} = 4,746873 \text{mA} \\ \hline & \text{SIEMENS} \ r_o = 18,26616 \text{k}\Omega \ V_A = 88,60728 \text{V} \ I_{C_{sat}} = 4,850897 \text{mA} \\ \hline & \text{modelo modificado} \ r_o = 17,34281 \text{k}\Omega \ V_A = 90,66048 \text{V} \ I_{C_{sat}} = 4,963302 \text{mA} \\ \hline & \text{transistor} \ 1 \ r_o = 19,97264 \text{k}\Omega \ V_A = 86,67009 \text{V} \ I_{C_{sat}} = 4,339440 \text{mA} \\ \hline & \text{transistor} \ 2 \ r_o = 22,66700 \text{k}\Omega \ V_A = 104,6125 \text{V} \ I_{C_{sat}} = 4,615188 \text{mA} \\ \hline & \text{transistor} \ 3 \ r_o = 23,13776 \text{k}\Omega \ V_A = 107,6684 \text{V} \ I_{C_{sat}} = 4,653361 \text{mA} \\ \hline \end{array}$

